



PTO/SB/08B (10-01)

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Substitute for form 1449B/PTO INFORMATION DISCLOSURE STATEMENT BY APPLICANT (use as many sheets as necessary)			Complete if Known		
			Application Number	Not Yet Assigned	
			Filing Date	April 16, 2004	
			First Named Inventor	Kristy A. Campbell, et al.	
			Group Art Unit	Not Yet Assigned	
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Sheet	1	of	9	Attorney Docket Number	M4065.0703/P703-A

U.S. PATENT DOCUMENTS					
Examiner Initials*	Cite No.†	Document Number Number-Kind Code* (if known)	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
DV	AA*	6,388,324	05/14/2002	Kozicki et al.	
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Substitute for form 1449B/PTO INFORMATION DISCLOSURE STATEMENT BY APPLICANT (use as many sheets as necessary)				Complete if Known	
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DV	AT1*	6,391,688 B1	05/21/2002	Gonzalez et al.	
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<input checked="" type="checkbox"/>		143 (2001) 445-455.	
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